

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known Application Number 10/624,959 Filing Date July 22, 2003 First Named Inventor Karen K. Gleason Art Unit 1711 Examiner Name Not Yet Assigned Attorney Docket Number 101328-180		
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	CW	2002/0042657 A1	04/11/2002	Pugh et al.	
	CX	2002/0062782 A1	05/30/2002	Norris et al.	
	CY	5,852,088	12/22/1998	Dismukes et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	†
		Country Code ² -Number-Kind Code ³ (if known)				
	DC	WO 01/86038 A2	11/15/2001	Universidad Politecnica De Valencia et al.		
	DD	WO 01/96635 A2	12/20/2001	Merck Patent GMBH		

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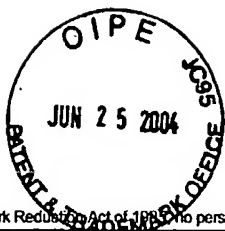
NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
	DG	Lanata, M. et al. "Titania Inverse Opals For Infrared Optical Applications" Optical Materials, Vol. 17, pps. 11-14 (2001);		
	DH	Yan, Hongwei et al. "Influence of Processing Conditions On Structures of 3D Ordered Macroporous Metals Prepared by Colloidal Crystal Templating" Chem. Mater., Vol. 13, pps. 4314-4321 (2001)		

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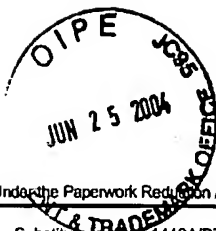
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				Application Number	10/624,959 (Conf #6293)
				Filing Date	July 22, 2003
				First Named Inventor	Karen K. Gleason
				Art Unit	Not Yet Assigned
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		Number-Kind Code ² (if known)			
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		Country-Number				
MF	BA	EP 1 321 976 A2	06/25/2003	Canon Sales Co., Inc.		
	BB	EP 1 148 539 A2	10/24/2001	Applied Materials, Inc.		
	BC	EP 1 195 451 A1	04/10/2002	Applied Materials, Inc.		
MF	BD	WO 03/005429 A1	01/16/2003	Postech Foundation		



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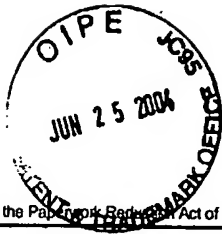
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				First Named Inventor	Karen K. Gleason
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				Examiner Name	Not Yet Assigned
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²		
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Examiner Signature		<i>[Signature]</i>	Date Considered 10/04

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